

**TECHNICAL BULLETIN**

Designed for Ultra Broadband RF/Microwave Power applications, this amplifier utilizes linear GaAsFET Power devices that provide high gain, wide dynamic range and excellent linearity. Exceptional performance, long term reliability and high efficiency are achieved by employing advanced broadband RF matching networks and combining techniques, EMI/RFI filters, custom-machined housings and qualified components. Each unit undergoes extensive burn-in prior to final test and inspection.

**SPECIFICATIONS @ VDD=13 VDC, Temp=25°C**

Characteristics	Range	Limit
Frequency Response	800 - 4200 MHz	Min
Power Output CW	1.3 Watt	Min
Power Output @ 1 dB comp.	1.0 Watt	Min
Third Order Intercept Point	+41 dBm	Typ
Small Signal Gain	30 dB	Min
Gain Flatness	±1.5 dB	Max
Noise Figure	10 dB	Max
Input/Output VSWR	2:1	Max
DC Input Current	700 mA	Max
Dimensions	3.2"x2.5"x0.7"	Max
Weight	0.5 lb.	Max

**ELECTRICAL CHARACTERISTICS**

Impedance Input/output: 50 Ohm  
 DC Input: 13 - 15 VDC nominal  
 Input Signal Format: CW/AM/FM/PM/Pulse/Digital  
 Harmonics: -20 dBc typical at 1 dB comp.  
 Spurious Signals: >60 dBc  
 Class of Operation: A linear  
 Load VSWR: Infinite; no damage  
 Connectors Input/Output: SMA Female  
**ENVIRONMENTAL CHARACTERISTICS**  
 Operating Temperature: 0°C to +50°C  
 Humidity: 95% relative without condensation  
 Altitude: 10,000 feet

OUTLINE DRAWING

